What Is Claimed Is:

1. A method of stabilizing parasitic capacitance in an LCD device, comprising the steps of:

providing a substrate;

forming a plurality of transversely expanding gate lines on the substrate;

forming a first insulating layer on the substrate and the gate lines;

performing a photolithography procedure using a photomask to form a plurality of longitudinally expanding data lines and a plurality of metallic light shield layers on part of the first insulating layer, wherein the metallic light shield layers are located on both sides of the data line;

forming a second insulating layer on the metallic light shield layers and the data lines; and

forming transparent conductive layers on part of the second insulating layer.

2. The method according to claim 1, further comprising the step of:

forming conductive plugs penetrating the second insulating layer to electrically connect the metallic light shield layers and the transparent conductive layers.

3. The method according to claim 1, wherein the substrate is a glass substrate.

4. The method according to claim 1, wherein the first insulating layer is a silicon oxide (SiO_x) layer.

5. The method according to claim 1, wherein the second insulating layer is a silicon oxide (SiO_x) layer.

6. The method according to claim 1, wherein the metallic light shield layers and the data lines comprise Al and/or Mo.

7. The method according to claim 1, wherein the transparent conductive layers are ITO (indium tin oxide) or IZO (indium zinc oxide) layers.

8. The method according to claim 2, wherein the metallic light shield layers and the transparent conductive layers are equipotential.

9. A method of stabilizing parasitic capacitance in an LCD device, comprising the steps of:

providing a glass substrate;

forming a plurality of transversely expanding gate lines on the glass substrate;

forming a first silicon oxide (SiO_x) layer on the glass substrate and the gate lines;

performing a photolithography procedure using a photomask to form a plurality of longitudinally expanding data lines and a plurality of metallic light shield layers on part of the first silicon oxide layer, wherein the metallic light shield layers are located on both sides of the data line;

forming a second silicon oxide (SiO_x) layer on the metallic light shield layers and the data lines;

forming conductive plugs penetrating the second silicon oxide layer; and

forming transparent conductive layers on part of the second silicon oxide layer, wherein the metallic light shield layers electrically connect the transparent conductive layers by means of the conductive plugs.

10. The method according to claim 9, wherein the metallic light shield layers and the data lines are equipotential.

11. The method according to claim 9, wherein the metallic light shield layers and the data lines comprise Al and/or Mo.

12. The method according to claim 9, wherein the transparent conductive layers are ITO (indium tin oxide) or IZO (indium zinc oxide) layers.